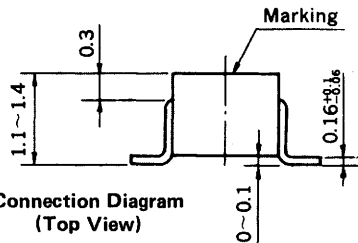
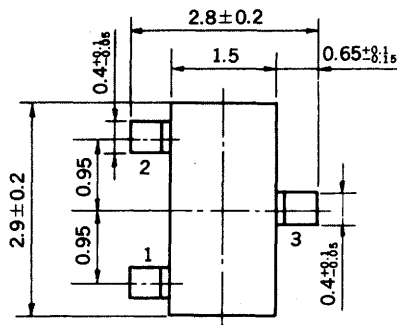
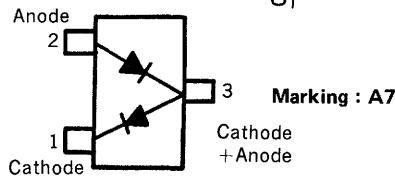


HIGH SPEED SWITCHING SILICON EPITAXIAL DOUBLE DIODES : SERIES CONNECTED MINI MOLD

PACKAGE DIMENSIONS in millimeters



Connection Diagram
(Top View)



FEATURES

- Low capacitance: $C_t = 4.0 \text{ pF MAX.}$
- High speed switching: $t_{rr} = 9.0 \text{ ns MAX.}$
- Wide applications including switching, limiter, clipper.
- Double diode configuration assures economical use.

ABSOLUTE MAXIMUM RATINGS

Maximum Voltages and Currents ($T_a = 25^\circ\text{C}$)

Peak Reverse Voltage	V_{RM}	70	V
DC Reverse Voltage	V_R	70	V
Peak Forward Current	I_{FM}	200	mA
Average Rectified Current	I_O	100	mA
DC Forward Current	I_F	100	mA

Maximum Temperatures

Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to +150	$^\circ\text{C}$

Thermal Resistance

Junction to Ambient*	$R_{th(j-a)}$	1.0	$^\circ\text{C/mW}$
Junction to Ambient	$R_{th(j-a)}$	0.67	$^\circ\text{C/mW}$

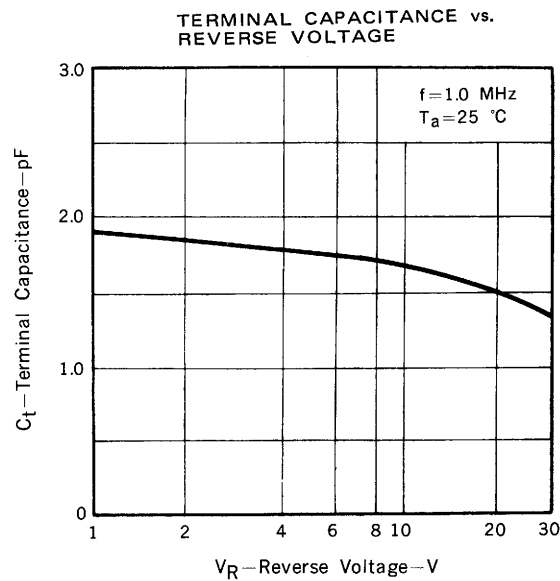
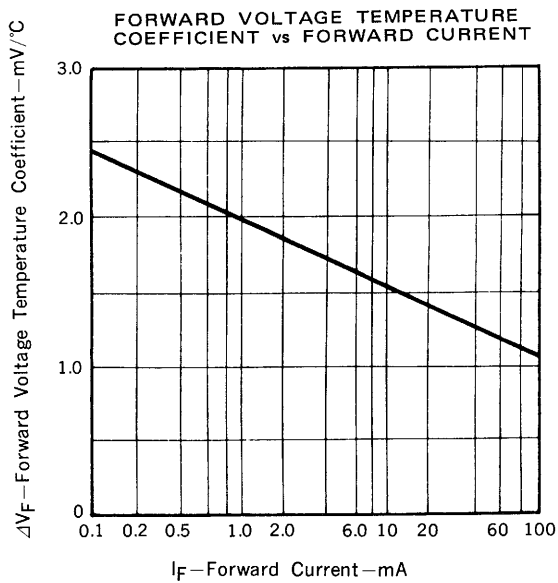
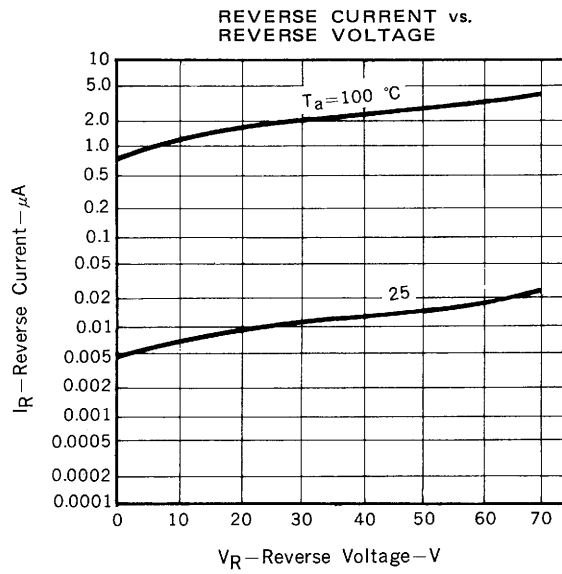
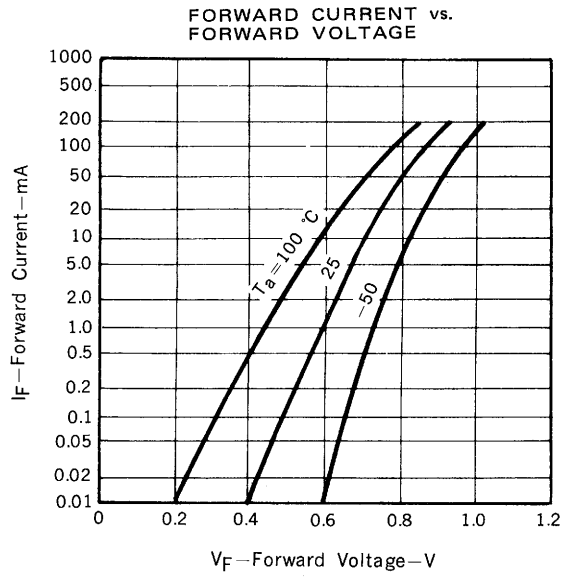
* Both diodes loaded simultaneously.

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Forward Voltage	V_{F1}		600	715	mV	$I_F = 1.0 \text{ mA}$
	V_{F2}		750	855	mV	$I_F = 10 \text{ mA}$
	V_{F3}		850	1100	mV	$I_F = 50 \text{ mA}$
	V_{F4}		900	1300	mV	$I_F = 100 \text{ mA}$
Reverse Current	I_R			1.0	μA	$V_R = 70 \text{ V}$
Capacitance	C_t		2.5	4.0	pF	$V_R = 0, f = 1.0 \text{ MHz}$
Reverse Recovery Time	t_{rr}			9.0	ns	$I_F = 10 \text{ mA}, V_R = 1 \text{ V}, R_L = 100 \Omega$ See test circuit.
Forward Recovery Voltage	V_{fr}			1.75	V	$I_F = 10 \text{ mA}$ See Test Circuit.

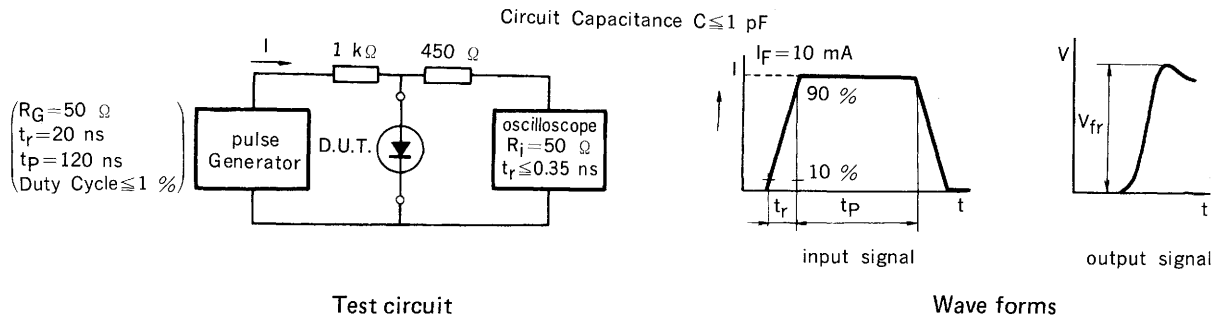
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TYPICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

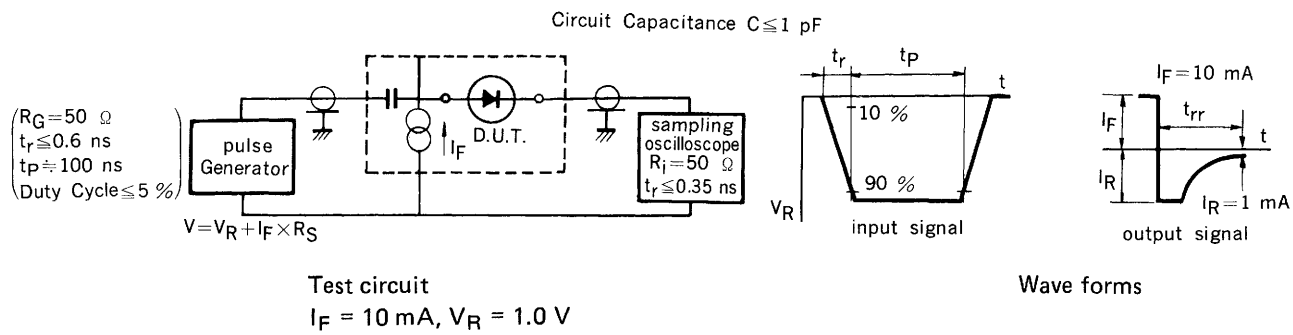


SWITCHING CHARACTERISTICS TEST CIRCUIT

Forward recovery voltage : V_{fr}



Reverse recovery time : t_{rr}



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